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June 2016

FOD410, FOD4108, FOD4116, FOD4118 6-Pin DIP Snubberless Zero-Cross Triac Drivers

Features

- · 300 mA On-State Current
- · Zero-Voltage Crossing
- · High Blocking Voltage
 - 600 V (FOD410, FOD4116)
 - 800 V (FOD4108, FOD4118)
- · High Trigger Sensitivity
 - 1.3 mA (FOD4116, FOD4118)
 - 2 mA (FOD410, FOD4108)
- High Static dv/dt (10,000 V/µs)
- Safety and Regulatory Approvals:
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5

Applications

- Solid-State Relays
- · Industrial Controls
- Lighting Controls
- · Static Power Switches
- · AC Motor Starters

Description

The FOD410, FOD4108, FOD4116 and FOD4118 devices consist of an infrared emitting diode coupled to a hybrid triac formed with two inverse parallel SCRs which form the triac function capable of driving discrete triacs. The FOD4116 and FOD4118 utilize a high efficiency infrared emitting diode which offers an improved trigger sensitivity. These devices are housed in a standard 6-pin dual in-line (DIP) package.

Functional Schematic

ANODE 1 CATHODE 2 N/C 3 *DO NOT CONNECT (TRIAC SUBSTRATE)

Package Outlines

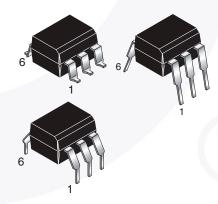


Figure 2. Package Outlines

Figure 1. Schematic

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter | Characteristics | |
|--|---|-----------|
| Installation Classifications per DIN VDE | on Classifications per DIN VDE < 150 V _{RMS} | |
| 0110/1.89 Table 1, For Rated Mains Voltage | < 300 V _{RMS} | I–IV |
| Climatic Classification | | 55/100/21 |
| Pollution Degree (DIN VDE 0110/1.89) | | 2 |
| Comparative Tracking Index | | 175 |

| Symbol | Parameter | Value | Unit |
|-----------------------|--|-------------------|-------------------|
| V | Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10 \text{ s}$, Partial Discharge < 5 pC | | V _{peak} |
| V _{PR} | Input-to-Output Test Voltage, Method B, V_{IORM} x 1.875 = V_{PR} , 100% Production Test with t_{m} = 1 s, Partial Discharge < 5 pC | 1594 | V _{peak} |
| V _{IORM} | Maximum Working Insulation Voltage | 850 | V _{peak} |
| V _{IOTM} | Highest Allowable Over-Voltage | 6000 | V _{peak} |
| | External Creepage | ≥ 7 | mm |
| | External Clearance | ≥ 7 | mm |
| DTI | Distance Through Insulation (Insulation Thickness) | ≥ 0.4 | mm |
| T _S | Case Temperature ⁽¹⁾ | 175 | °C |
| I _{S,INPUT} | Input Current ⁽¹⁾ | 400 | mA |
| P _{S,OUTPUT} | Output Power ⁽¹⁾ | 700 | mW |
| R _{IO} | Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾ | > 10 ⁹ | Ω |

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ unless otherwise specified.

| Symbol | Parameter | Device | Value | Unit |
|--------------------------|--|------------------|----------------|-------|
| T _{STG} | Storage Temperature | All | -55 to +150 | °C |
| T _{OPR} | Operating Temperature | All | -55 to +100 | °C |
| T _J | Junction Temperature | All | -55 to +125 | °C |
| T _{SOL} | Lead Solder Temperature | All | 260 for 10 sec | °C |
| В | Total Device Power Dissipation @ 25°C | All | 500 | mW |
| P _{D(TOTAL)} | Derate Above 25°C | All | 6.6 | mW/°C |
| EMITTER | | | | |
| I _F | Continuous Forward Current | All | 30 | А |
| V _R | Reverse Voltage | All | 6 | V |
| Б | Total Power Dissipation 25°C Ambient | All | 50 | mW |
| P _{D(EMITTER)} | Derate Above 25°C | All | 0.71 | mW/°C |
| DETECTOR | | | | |
| | Off Chata Output Tampinal Valtage | FOD410, FOD4116 | 600 | V |
| V_{DRM} | Off-State Output Terminal Voltage | FOD4108, FOD4118 | 800 | V |
| I _{TSM} | Peak Non-Repetitive Surge Current (single cycle 60 Hz sine wave) | All | 3 | Α |
| I _{TM} | Peak On-State Current | All | 300 | mA |
| р | Total Power Dissipation @ 25°C Ambient | All | 450 | mW |
| P _{D(DETECTOR)} | Derate Above 25°C | All | 5.9 | mW/°C |

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Individual Component Characteristics

| Symbol | Parameter | Test Cor | nditions | Device | Min. | Тур. | Max. | Unit |
|---------------------|--|--|------------------------|---------------------|--------|--------|------|------|
| EMITTER | <u>.</u> | • | | • | | | | |
| V _F | Input Forward Voltage | I _F = 20 mA | I _F = 20 mA | | | 1.25 | 1.50 | V |
| I _R | Reverse Leakage Current | V _R = 6 V | V _R = 6 V | | | 0.0001 | 10 | μA |
| DETECTOR | | | | | | | | |
| | Peak Blocking Current Either | ling Current Either $I_F = 0$, $T_A = 100^{\circ}C^{(2)}$ | V _D = 600 V | FOD410, FOD4116 | | 3 | 100 | μΑ |
| I _{D(RMS)} | Direction | | V _D = 800 V | FOD4108, FOD4118 | | | | |
| | | T _A = 100°C | V _D = 600 V | FOD410, FOD4116 | | 3 | 400 | |
| I _{R(RMS)} | Reverse Current | | V _D = 800 V | FOD4108, FOD4118 | | 3 | 100 | μΑ |
| dv/dt | Critical Rate of Rise of Off-State Voltage | I _F = 0 ⁽³⁾ (Figure 15) | | All | 10,000 | | | V/µs |

Notes:

- 2. Test voltage must be applied within dv/dt rating.
- 3. This is static dv/dt. See Figure 15 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.

Electrical Characteristics (Continued)

 $T_A = 25$ °C unless otherwise specified.

Transfer Characteristics

| Symbol | Parameter | Test | Conditions | Device | Min. | Тур. | Max. | Unit | | | | |
|----------------------|--|--|---|--------------------------------|-------------------------|--------|---|--------------------------------|---|----|--|----|
| I _{FT} | LED Trigger Current | Main Terminal Volt | Main Terminal Voltage = 5 V ⁽⁴⁾ | | | 0.65 | 2.0 | mA | | | | |
| 'FT | LLD Higger Current | Iviairi Terriiriai Voit | age = 5 v · · | FOD4116, FOD4118 | | 0.65 | 1.3 | IIIA | | | | |
| V _{TM} | Peak On-State Voltage, Either Direction | I _{TM} = 300 mA peal | k, I _F = Rated I _{FT} | All | | 2.2 | 3 | V | | | | |
| I _H | Holding Current, Either Direction | V _T = 3 V | | All | | 200 | 500 | μΑ | | | | |
| IL | Latching Current | V _T = 2.2 V | | All | | 5 | | mA | | | | |
| t _{ON} | Turn-On Time | | V _{RM} = V _{DM} = 424 VAC | FOD410, FOD4116, FOD4118 | | 60 | | μs | | | | |
| | | PF = 1.0, | $V_{RM} = V_{DM} = 565 \text{ VAC}$ | FOD4108 | | | | | | | | |
| t _{OFF} | Turn-Off Time | I _T = 300 mA | I _T = 300 mA | I _T = 300 mA | I _T = 300 mA | | V _{RM} = V _{DM} = 424 VAC | FOD410, FOD4116, FOD4118 | , | 52 | | μs |
| | | | $V_{RM} = V_{DM} = 565 \text{ VAC}$ | FOD4108 | | | | | | | | |
| al. (/al& | Critical Rate of Rise of | $V_{D} = 0.67 V_{DRM}$ | T _J = 25°C | A.II | 10,000 | | | V/µs | | | | |
| dv/dt _{crq} | Voltage at Current Com- mutation di/dt _{crq} ≤ 15 A/ms | | T _J = 80°C | All | 5,000 | | | V/µs | | | | |
| di/dt _{cr} | Critical Rate of Rise of On-State Current | , | | All | | | 8 | A/µs | | | | |
| dv(IO)/dt | Critical Rate of Rise of Coupled Input/Output Voltage | I _T = 0 A, V _{RM =} V _D | _T = 0 A, V _{RM =} V _{DM} = 424 VAC | | | 10,000 | | V/µs | | | | |

Note:

4. All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT}. Therefore, recommended operating I_F lies between max I_{FT} (2 mA for FOD410 and FOD4108 and 1.3 mA for FOD4116 and FOD4118) and the absolute max I_F (60 mA).

Zero Crossing Characteristics

| Symbol | Parameter | Test Conditions | Device | Min. | Тур. | Max. | Unit |
|-------------------|--|---|--------|------|------|------|------|
| V _{INH} | Inhibit Voltage (MT1-MT2 Voltage above which device will not trigger) | I _F = Rated I _{FT} | All | | 8 | 25 | > |
| I _{DRM2} | Leakage in Inhibit State | I _F = Rated I _{FT} , Rated V _{DRM} , Off-State | All | | 20 | 200 | μΑ |

Isolation Characteristics

| Syr | nbol | Parameter | Test Conditions | Device | Min. | Тур. | Max. | Unit |
|-----|------|-----------------------------------|--|--------|-------|------|------|--------------------|
| V | 130 | Steady State Isolation Voltage | f = 60 Hz, t = 1 Minute ⁽⁵⁾ | All | 5,000 | | | VAC _{RMS} |

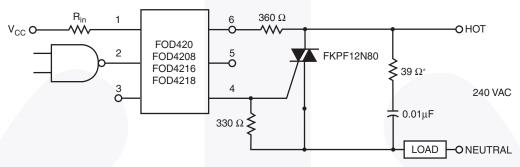
Note:

5. Isolation voltage, V_{ISO} , is an internal device dielectric breakdown rating. For this test, pins 1, 2 and 3 are common, and pins 4, 5 and 6 are common. 5,000 VAC_{RMS} for 1 minute duration is equivalent to 6,000 VAC_{RMS} for 1 second duration.

Typical Application

Figure 3 shows a typical circuit for when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

 R_{in} is calculated so that I_F is equal to the rated I_{FT} of the part, 2 mA for FOD420 and FOD4208, 1.3 mA for FOD4216 and FOD4218. The 39 Ω resistor and 0.01 μF capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.



* For highly inductive loads (power factor < 0.5), change this value to 360 ohms.

Figure 3. Hot-Line Switching Application Circuit

Typical Performance Characteristics IFT - NORMALIZED LED TRIGGER CURRENT V_{AK} = 5.0 V Normalized to T_A = 25°C V_F – FORWARD VOLTAGE (V) 1.4 -55°C 1.2 25°C 1.0 1.0 0.8 0.8 0.6 20 40 60 10 100 I_F – FORWARD CURRENT (mA) T_A - AMBIENT TEMPERATURE (°C) Figure 4. Forward Voltage (V_F) Figure 5. Normalized LED Trigger Current (IFT) vs. Forward Current (I_F) vs. Ambient Temperature (T_A) 100 10000 $t_D = t(I_F/I_{FT\ 25^{\circ}C})$ $V_D = 400\ V_{P-P}$ $F = 60\ Hz$ If(pk) - PEAK LED CURRENT (mA) **Duty Factor** 0.005 t_D – DELAY TIME (µs) 0.01 1000 0.02 10 0.2 100 10 -6 10-6 10-3 10⁻² 10-1 100 t - LED PULSE DURATION (s) I_{FT}/I_F - NORMALIZED I_F (mA) Figure 6. Peak LED Current Figure 7. Trigger Delay Time vs. Duty Factor, Tau 1000 1.7 IFTH(PW)/IFTH(DC) - NORMALIZED IFTH V_L = 250 V_{P-P} F = 60 Hz 1.6 I_{TM} – ON-STATE CURRENT (mA) Normalized to DC 1.5 100 1.4 1.3 T_A = 100°C 1.2 T_A = 25°C 10 1.1 1.0 0.9 0 200 600 800 1000 0 3 P_W – PULSE WIDTH (μs) V_{TM} – ON-STATE VOLTAGE (V) Figure 8. Pulse Trigger Current Figure 9. On-State Voltage (V_{TM}) vs. On-State Current (I_{TM})

Typical Performance Characteristics (Continued)

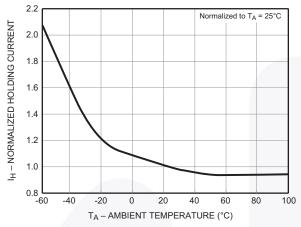


Figure 10. Normalized Holding Current (I_H) vs. Ambient Temperature (T_A)

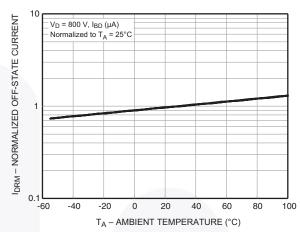


Figure 11. Normalized Off-State Current (I_{DRM}) vs. Ambient Temperature (T_A)

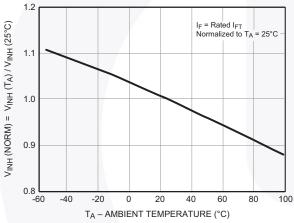


Figure 12. Normalized Inhibit Voltage (V_{INH}) vs. Ambient Temperature (T_A)

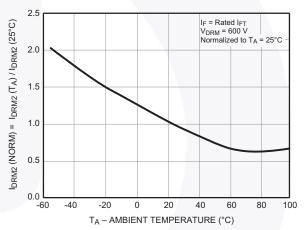


Figure 13. Normalized Leakage in Inhibit State (I_{DRM2}) vs. Ambient Temperature (T_A)

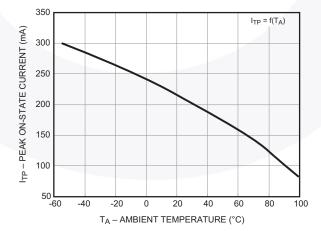
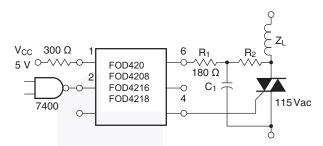


Figure 14. Current Reduction



NOTE: Circuit supplies 25 mA drive to gate of triac at V_{in} = 25 V and T_A < 70°C

| | TRIAC | | | | |
|----------------------|--------------------|---------------------|--|--|--|
| I _{GT} (mA) | R ₂ (Ω) | C ₁ (uF) | | | |
| 15 | 2400 | 0.1 | | | |
| 30 | 1200 | 0.2 | | | |
| 50 | 800 | 0.3 | | | |

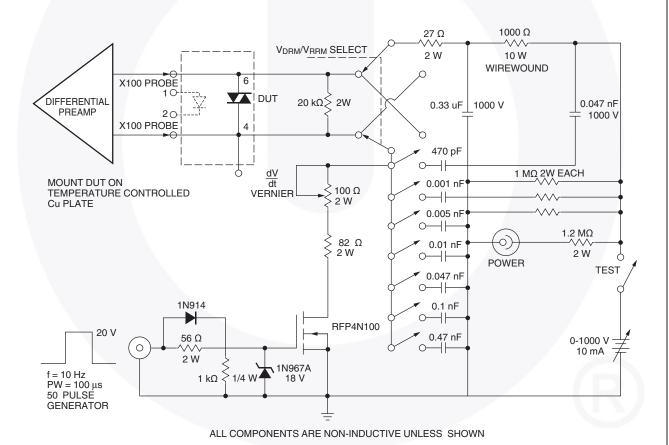


Figure 13. Circuit for Static $\frac{dv}{dt}$ Measurement of Power Thyristors

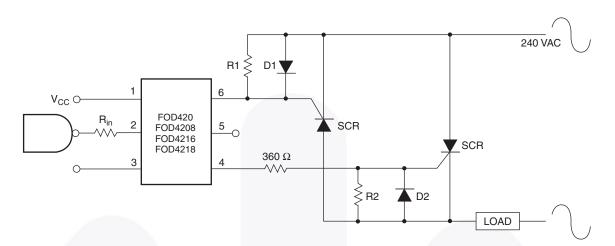
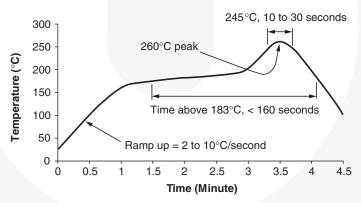


Figure 14. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330Ω .

Note: This optoisolator should not be used to drive a load directly. It is intended to be a discrete triac driver device only.

Reflow Profile



- Peak reflow temperature: 260°C (package surface temperature)
- Time of temperature higher than 183°C for 160 seconds or less
- One time soldering reflow is recommended

Figure 15. Reflow Profile

Ordering Information

| Part Number | Package | Packing Method |
|-------------|--|----------------------------|
| FOD410 | DIP 6-Pin | Tube (50 Units) |
| FOD410S | SMT 6-Pin (Lead Bend) | Tube (50 Units) |
| FOD410SD | SMT 6-Pin (Lead Bend) | Tape and Reel (1000 Units) |
| FOD410V | DIP 6-Pin, DIN EN/IEC60747-5-5 Option | Tube (50 Units) |
| FOD410SV | SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option | Tube (50 Units) |
| FOD410SDV | SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option | Tape and Reel (1000 Units) |
| FOD410TV | DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option | Tube (50 Units) |

Note:

6. The product orderable part number system listed in this table also applies to the FOD4108, FOD4116, and FOD4118 product families.

Marking Information

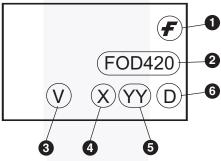
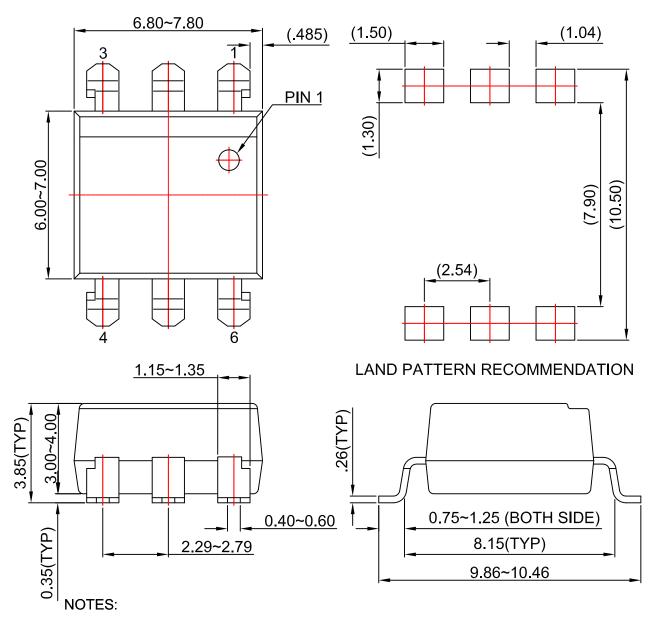


Figure 18. Top Mark

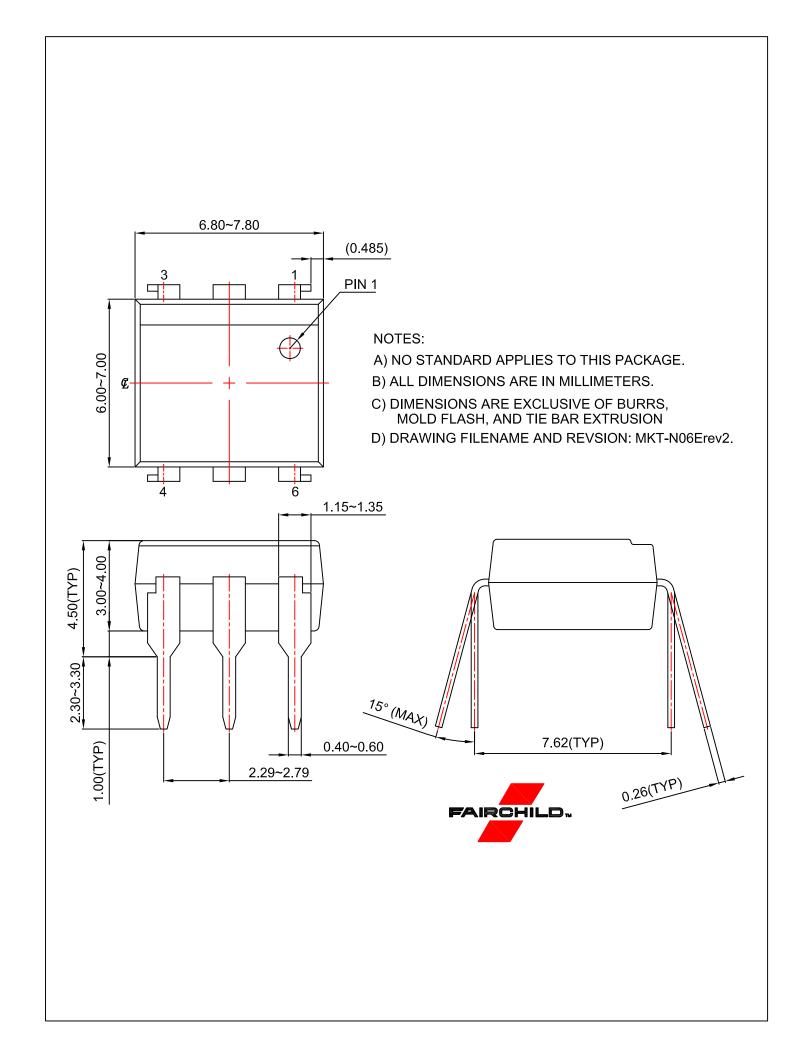
Table 1. Top Mark Definitions

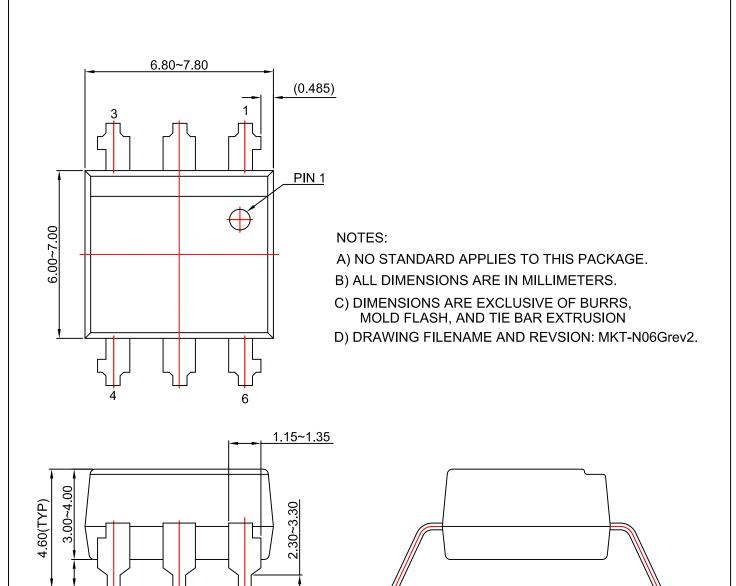
| 1 | Fairchild Logo |
|---|---|
| 2 | Device Number |
| 3 | VDE mark. DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option) |
| 4 | One-Digit Year Code, e.g., "6" |
| 5 | Digit Work Week, Ranging from "01" to "53" |
| 6 | Assembly Package Code |



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